



ATP112

P-Channel Power MOSFET -60V, -25A, 43mΩ, Single ATPAK

ON Semiconductor®

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Features

- ON-resistance $R_{DS(on)1}=33m\Omega$ (typ.)
- 4V drive
- Protection diode in
- Input Capacitance $C_{iss}=1450pF$ (typ.)
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-60	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		-25	A
Drain Current ($PW \leq 10\mu s$)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-75	A
Allowable Power Dissipation	P_D	$T_c=25^\circ C$	40	W
Channel Temperature	T_{ch}		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	E_{AS}		50	mJ
Avalanche Current *2	I_{AV}		-13	A

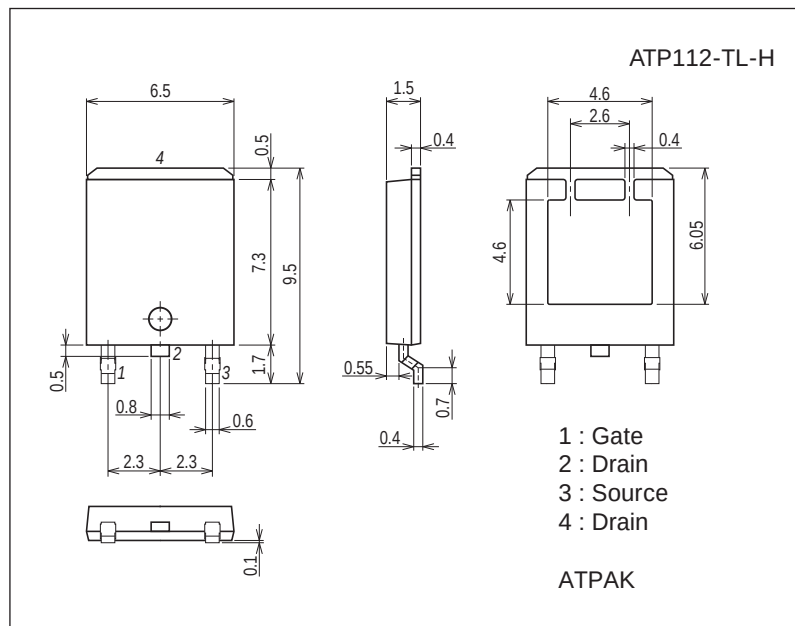
Note : *1 $V_{DD}=-10V$, $L=500\mu H$, $I_{AV}=-13A$ *2 $L \leq 500\mu H$, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

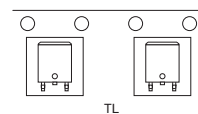
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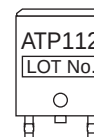
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

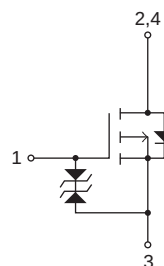
Packing Type: TL



Marking



Electrical Connection

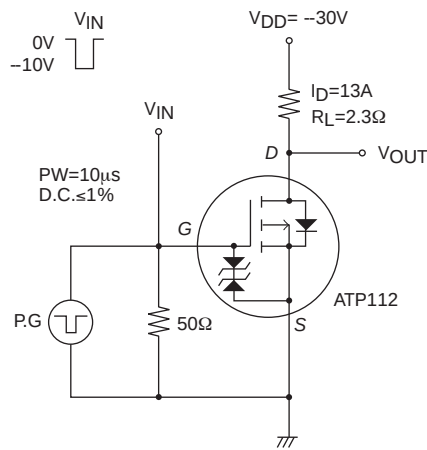


ATP112

Electrical Characteristics at Ta=25°C

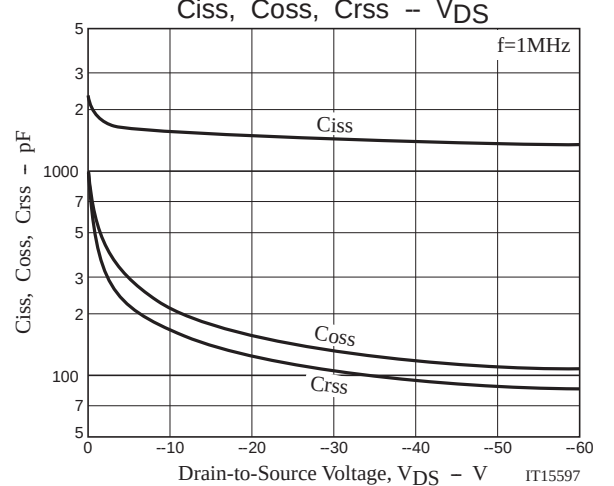
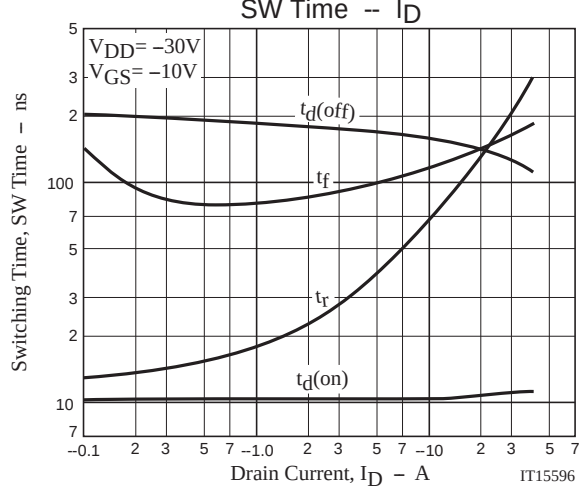
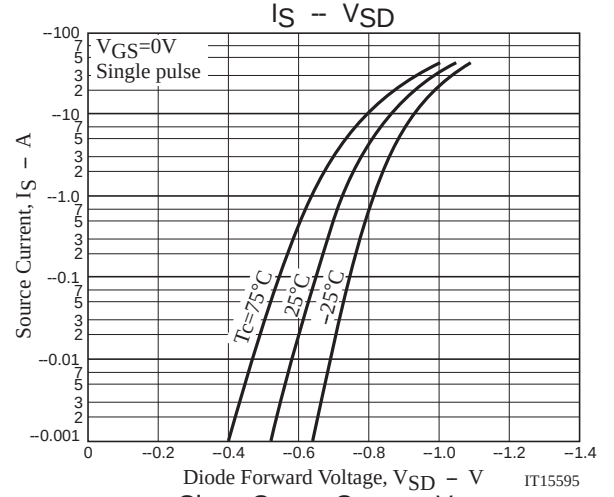
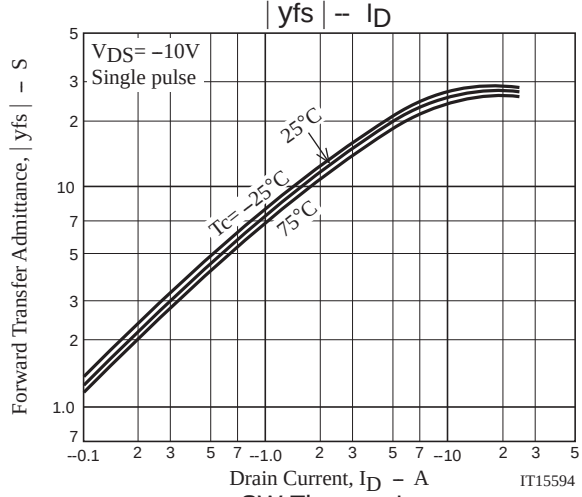
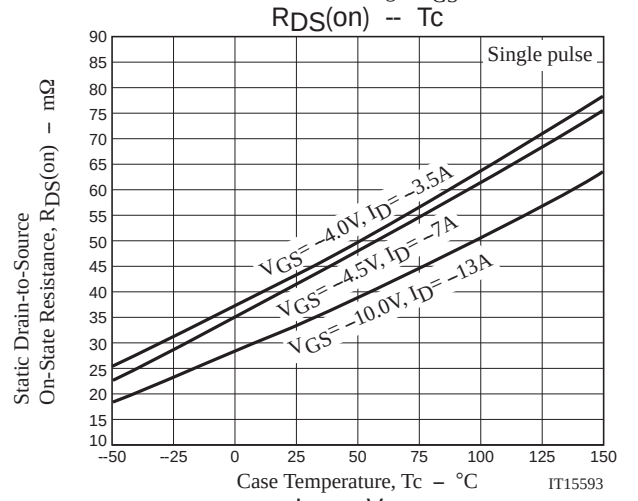
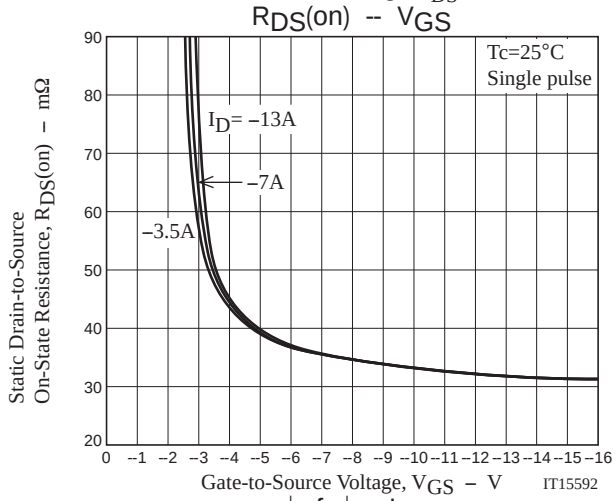
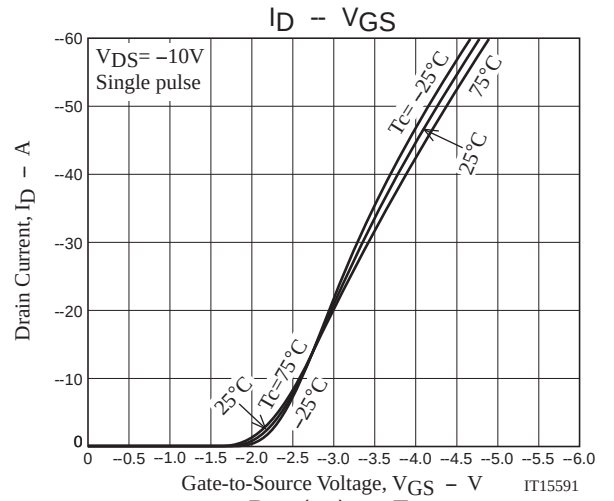
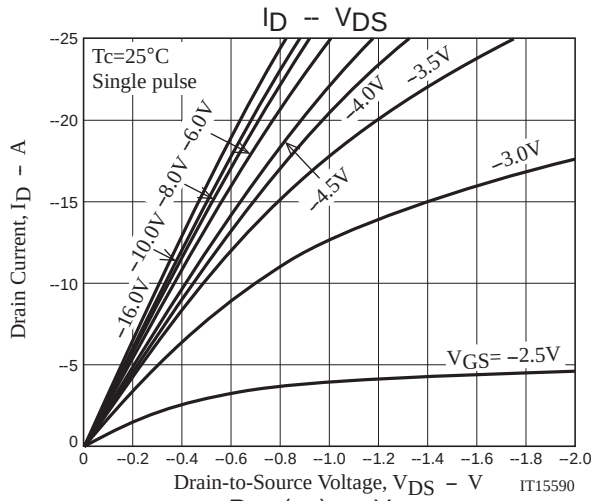
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0V$	-60			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-13A$		24		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-13A, V_{GS}=-10V$		33	43	$m\Omega$
	$R_{DS(on)2}$	$I_D=-7A, V_{GS}=-4.5V$		42	59	$m\Omega$
	$R_{DS(on)3}$	$I_D=-3.5A, V_{GS}=-4V$		45	63	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-20V, f=1MHz$		1450		pF
Output Capacitance	C_{oss}			155		pF
Reverse Transfer Capacitance	C_{rss}			125		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		10		ns
Rise Time	t_r			80		ns
Turn-OFF Delay Time	$t_d(off)$			150		ns
Fall Time	t_f			120		ns
Total Gate Charge	Q_g	$V_{DS}=-30V, V_{GS}=-10V, I_D=-25A$		33.5		nC
Gate-to-Source Charge	Q_{gs}			5.3		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			7.9		nC
Diode Forward Voltage	V_{SD}	$I_S=-25A, V_{GS}=0V$		-0.97	-1.5	V

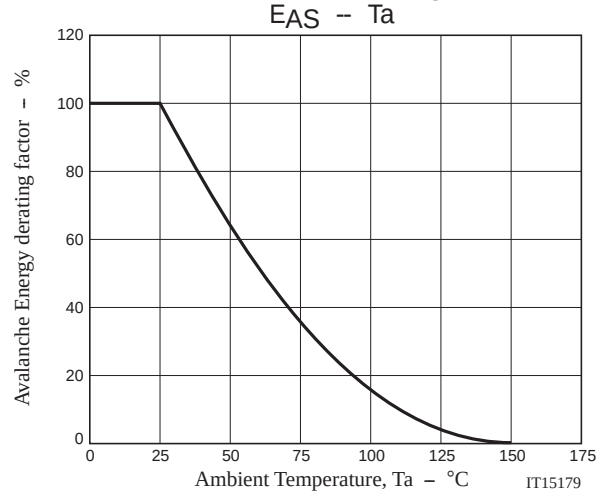
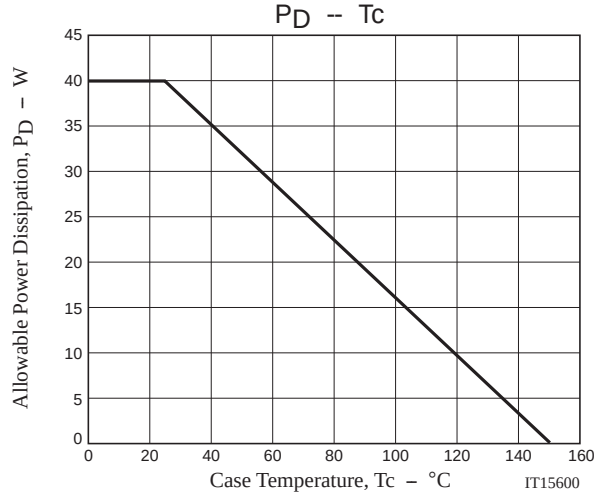
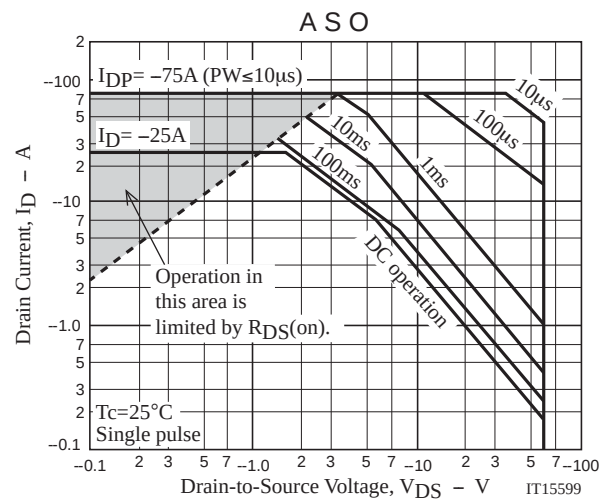
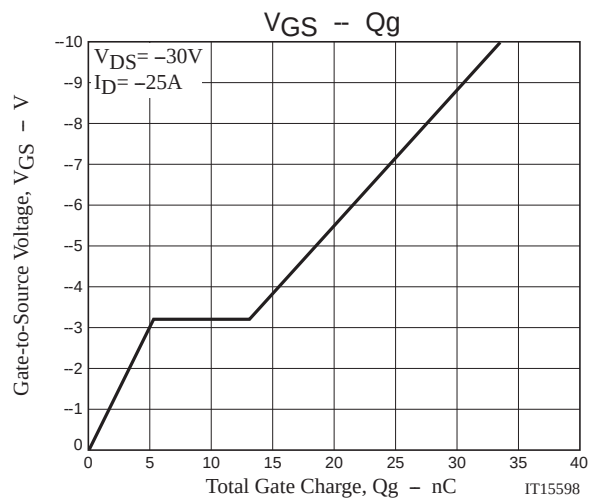
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ATP112-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free



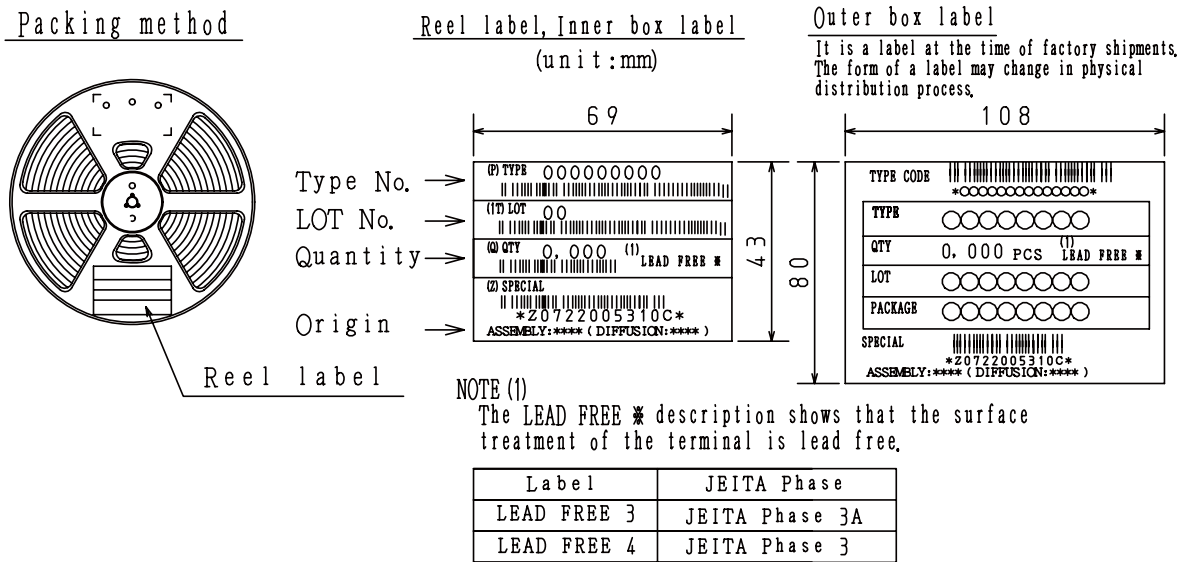


Taping Specification

ATP112-TL-H

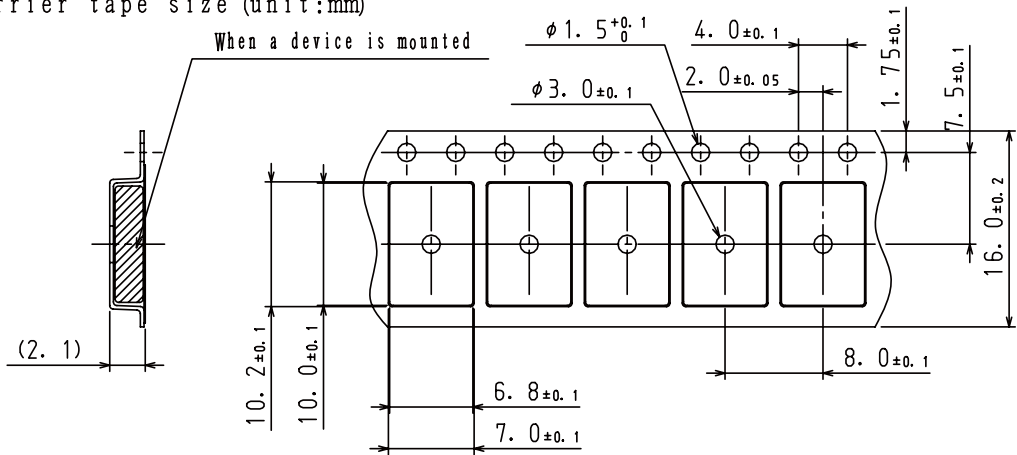
1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

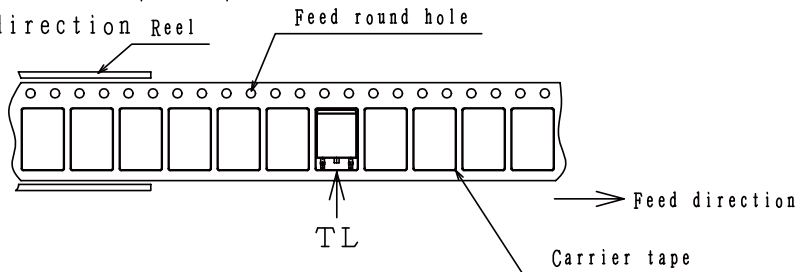


2. Taping configuration

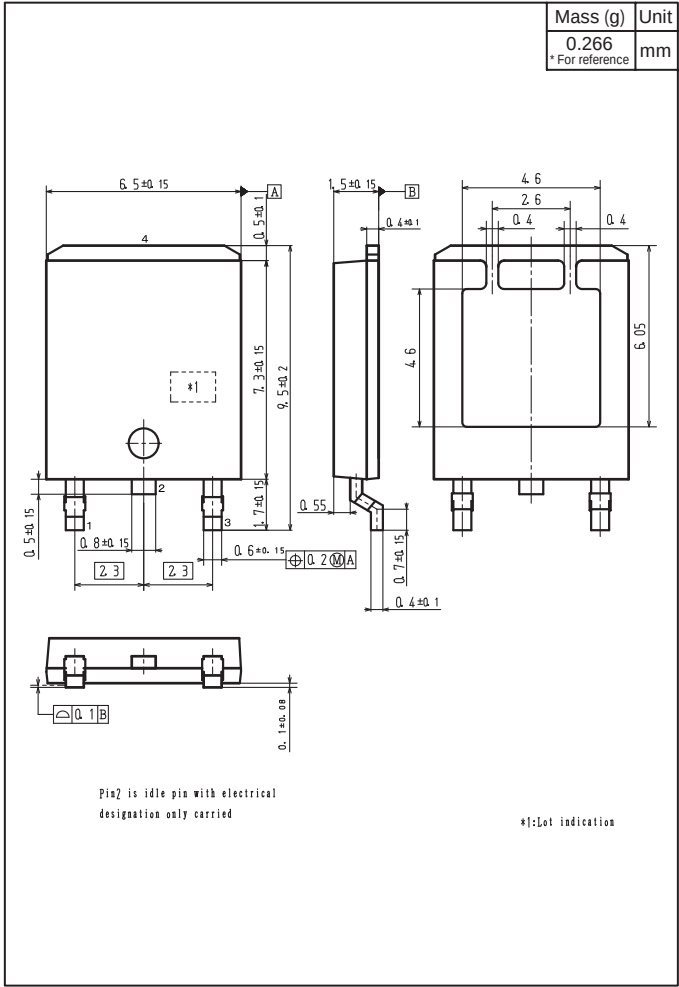
2-1. Carrier tape size (unit:mm)



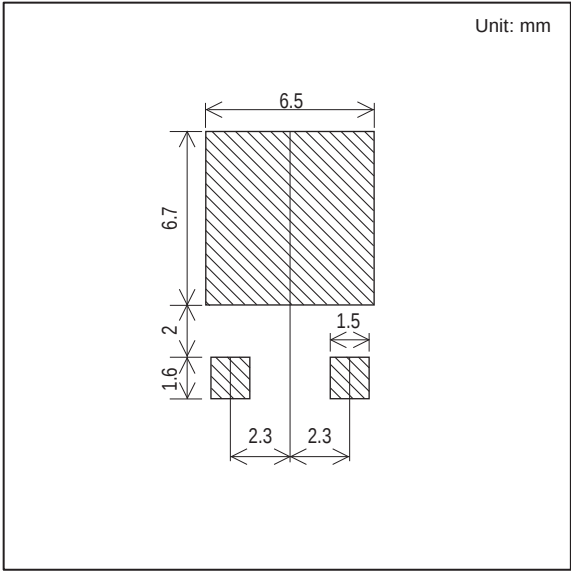
2-2. Device placement direction Reel



Outline Drawing
ATP112-TL-H



Land Pattern Example



Note on usage : Since the ATP112 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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